

ABSTRACT OF THE DISCLOSURE

The invention relates to a process for
5 obtaining a thin layer made of a first material on a
substrate made of a second material called the final
substrate, including the following steps:

- bonding a thick layer of a first material
on one of its main faces on the final substrate at an
10 interface,

- implantation of gaseous species in the
thick layer of first material to create a weakened zone
delimiting said thin layer between the interface and
the weakened zone,

15 - deposit a layer of third material called
the self-supporting layer on the thick layer made of
first material,

- fracture within the structure composed of
the final substrate, the thick layer of first material
20 and the layer of third material, at the weakened zone
to supply the substrate supporting said thin layer.

No Figure